Title (en)

SCHOTTKY-DIODE SEMICONDUCTOR DEVICE

Title (de)

HALBLEITER SCHOTTKYDIODE

Title (fr)

DISPOSITIF SEMI-CONDUCTEUR DU TYPE DIODE SCHOTTKY

Publication

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Application

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Abstract (en)

[origin: WO0178152A2] The invention concerns a Schottky-diode semiconductor device, comprising a substrate consisting of first (2) and second (3) semiconductor layers having the same type of conduction tiered up in said substrate, the second layer (3) being more highly doped than the first (2), said substrate having first (4) and second (5) main surfaces in contact with first (8) and second (6) electrodes, a Schottky barrier being formed between the first electrode (8) and said first layer. The invention is characterised in that the plurality of islands (9) having a type of conduction opposite to that of the first layer (2) are arranged in beds spaced apart in the thickness of said layer (2).

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